

Materials and Process Engineering for Printed and Flexible Opto-electronic Devices

Antonio Facchetti

Northwestern University and Polyera Corporation (USA)



Outline

- **Part 1. Polyera Corporation and Introduction to Printed Opto-Electronics**
- **Part 2. Organic Transistors**
 - **Structure and Operation**
 - **Materials and Process Requirements**
 - **Applications Printed TFTs and Circuits**
- **Part 3. Organic Solar Cells**
 - **Bulk-Heterojunction Structure**
 - **Printing Modules**
- **Conclusions**
- **Acknowledgements**

Part 1.

Polyera Corporation

Company Overview

Our History

- Founded in August 2005 from NU technologies
- Efforts in OTFT (2005), OPV (2008), Oxide Semiconductors/OLETs (2011)

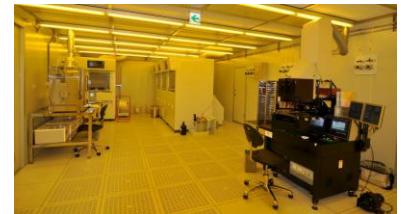
Our Facilities

- Skokie, USA
- Hsinchu, Taiwan

Chemistry and Materials Dev.



Formulation and Prototyping



Our Team

- Currently 61 employees
- 48 employees in R&D / technical support (25 PhDs)

Our Funding

- \$4MM Series A, Dec 2007
- \$5MM Series B, Aug 2010
- \$24.5MM Series C, March 2012

Our Mission

Be a supplier of functional materials to the solution-processed semiconductor industry

Polyera Corporation. Materials Portfolio



Core R&D Business

**Organic
Transistors**

Printed Electronics

**Organic
Photovoltaics**

Printed Solar Cells

**Oxide
Circuits**

Oxide TFTs

**CNT
Transistors**

**Organic
Light-Emitting
Transistors**

Printed Opto-Electronics

Fabricate (part of) opto-electronic devices using printing instead of vapor phase deposition/photolithography processes

Conventional Technology

- Very High Performance
- High Temperature Process
- Small Area
- Rigid/Breakable Devices
- High Capital Investment
- Long Production Run

Printed Technology

- Less Performance Are Needed
- Low Temperature Process
- Large Area
- Flexible Devices
- Short Production Run
- Designed for revolutionary products

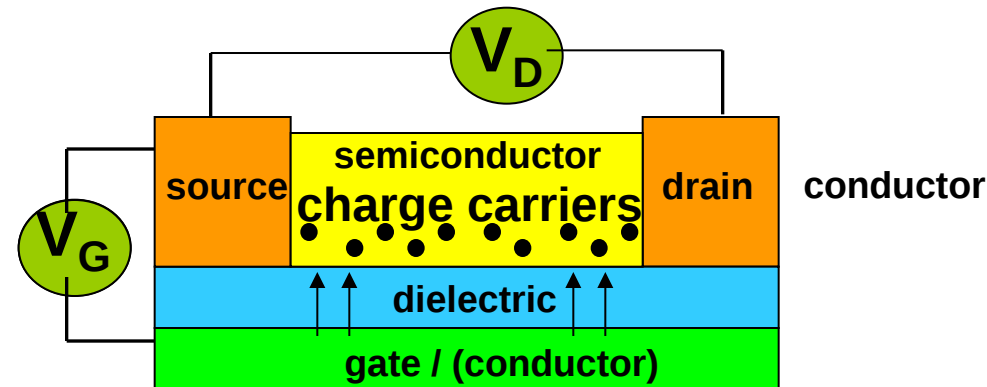
Science/Materials/Engineering Challenges

- Enhance Materials Performance
- Materials Formulated for Roll-to-Roll Processes, Environmentally Acceptable Solvents
- Maintain Performance on Inexpensive Substrates, Flexible Plastics
- Fabricate Commercially-relevant Device Architectures
- Understand Phenomena Based on Charge/Light-Soft Matter Interactions

Part 2.

Organic Transistors

Thin-Film Transistors Structure/Operation

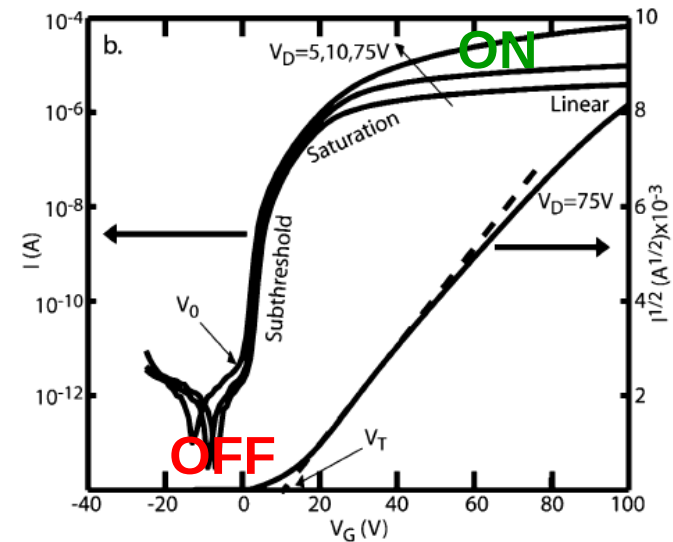


OFF
 $V_G = 0$

**NO CHARGE CARRIERS
BETWEEN s AND d $\Rightarrow I_D = 0$**

ON
 $V_G \neq 0$

**CREATES CHARGE CHANNEL IN
THE SEMICONDUCTOR LAYER
 $\Rightarrow I_D \neq 0$**



Carriers: hole = p-channel (type); electrons = n-channel (type)

The key performance parameter is the Carrier mobility (μ)

Printed TFTs need Printable p-/n-Semiconductors/Conductors/Dielectrics

Opportunities for Organic/Printed Transistors

**Low-Temperature
Fabrication**

Fabrication on plastics, Energy saving

Additive Process

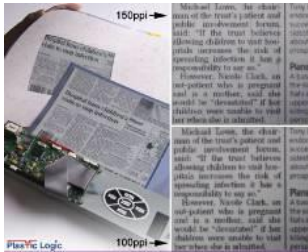
No materials waste

New Products

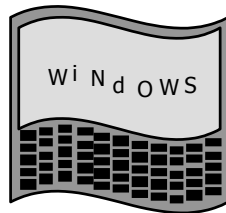
Inexpensive device assembly, Flexibility

Rigid, heavy and breakable -> Light, unbreakable and flexible

 Ground-breaking New SAMSUNG Flexible AMOLED Screen



**Rollable
Newspapers**



**Paper
Computer**



Rollable Display



Military



Printed Circuits, RFID



a-Si Carrier Mobility $\sim 0.5\text{-}1 \text{ cm}^2/\text{Vs}$ is sufficient!

Transistor Performance Optimization

**Great Opportunities for both Science and Technology
and to collaborate!**

Semiconductor

=> **Modify chemical structure**

=> **Vary film deposition parameters**

Facchetti, Husta *Adv. Mater.* **2012**, 24, 3678

Facchetti, Marks, Ratner, Wasielewski, *Adv. Mater.* **2011**, 23, 268

Facchetti, Kanatzidis, Marks, T. J. *Nature Mater.* **2011**, 10, 382

Facchetti, Muccini *Nature Mater.* **2010**, 9, 496

Facchetti, Morpurgo, *J. Am. Chem. Soc.* **2009**, 131, 2462

Facchetti, Y

2. Physics

1. Chemistry

Conductor

=> **Workfunction**

Facchetti, Sirringhaus *Chem Mater* **2010**, 22, 1559

Facchetti, Muccini *J. Phys. Chem.*

5. Prototyping

Device Design

=> **Structure**

=> **Geometry**

Noh, Facchetti *Organic Electronics* **2013**

Facchetti, A.; Noh, Y.-Y. *J. Pol. Sci. Pol. Phys.* **2011**, 49, 62

Facchetti, Marks *APL* **2009**,

4. Integration

Facchetti, Marks *APL* **2008**,
93, 263303

3. Process Engineering

Dielectric

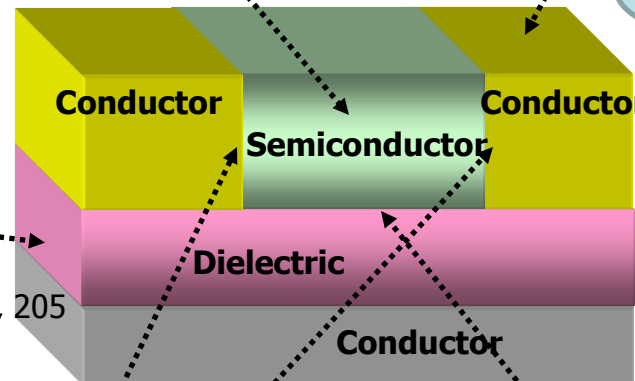
=> **Morphology, leakage, k**

Facchetti, Ponce, Marks *Chemical Reviews* **2010**, 110, 205

Facchetti, Marks *Chem. Mater.* **2009**, 21, 1173

Facchetti, Marks *J. Am. Chem. Soc.*, **2008**, 130, 6867

Facchetti, Marks *PNAS*. **2005**, 102, 4678.



Contact-Semiconductor Interface

Facchetti, Morpurgo *Appl. Phys. Lett.* **2010**, 97, 143307

Facchetti, Schol *Adv. Funct. Mater.* **2008**, 18, 3645

Facchetti, Marks *Nano Letters*. **2006**, 6, 2447

Dielectric-Semiconductor Interface

Facchetti, Marks *Adv. Funct. Mater.* **2010**, 20, 50

Facchetti, Marks Salleo *Nature Mater.*, **2009**, 8, 952

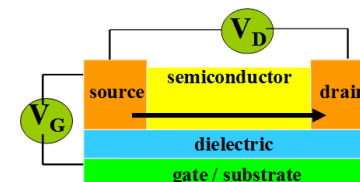
Facchetti, Marks *Science* **2007**, 318, 76.

1. Chemistry: Materials Design, Synthesis, Screening

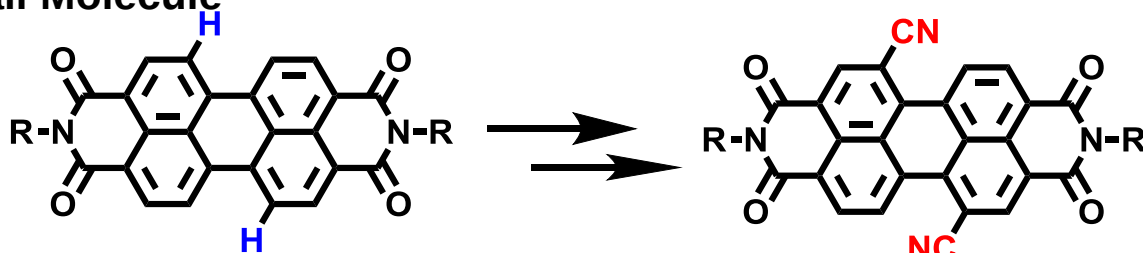
Semiconductor: Small Molecule, Polymers

Criteria For Achieving High Performance

- Proper HOMO/LUMO energy level
- Sufficient intermolecular interactions
- Favorable film morphology

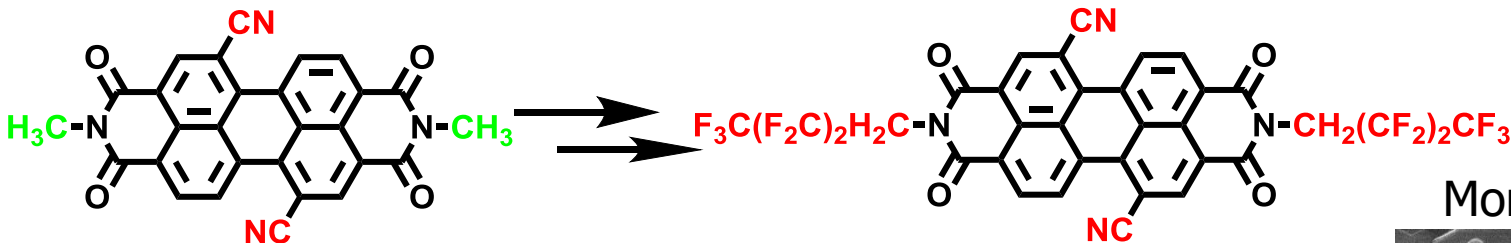


Small Molecule



Air unstable

Air stable !



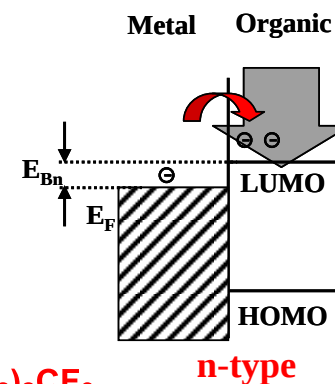
Low-Mobility

$$\mu \sim 0.000001 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$$

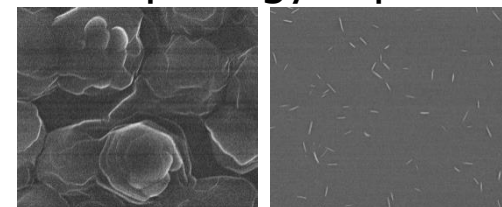
High-Mobility!

$$\mu \sim 1 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$$

Energetic aspect



Morphology aspect



Facchetti, Wasielewski, Marks et.al. *Angew. Chem., Int. Ed.* **2003**, 42, 3900

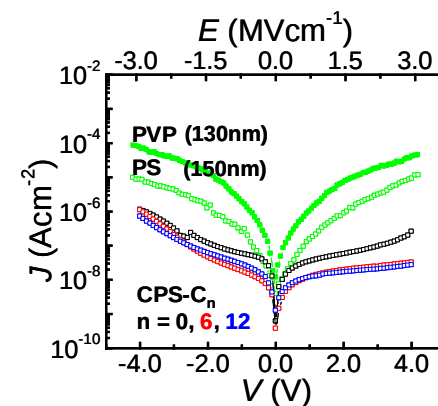
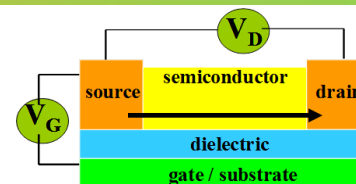
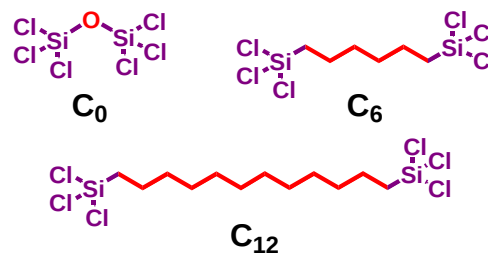
Facchetti, Marks, Wasielewski et.al. *Chem. Mater.* **2007**, 19, 2703

1. Chemistry: Molecular Design, Synthesis, Screening

Dielectric: Molecular, Polymeric, Hybrid

Criteria For Achieving High Performance

- Excellent insulator
- High capacitance
- Good morphology
- Good adhesion

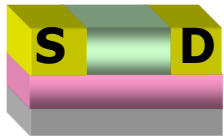


Conductors: Molecular, Polymeric, Hybrid

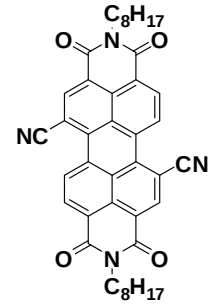
Criteria For Achieving High Performance

- High conductivity
- Good charge injection (SD)
- Low/reproducible contact resistance (S/D)
- Stable interface

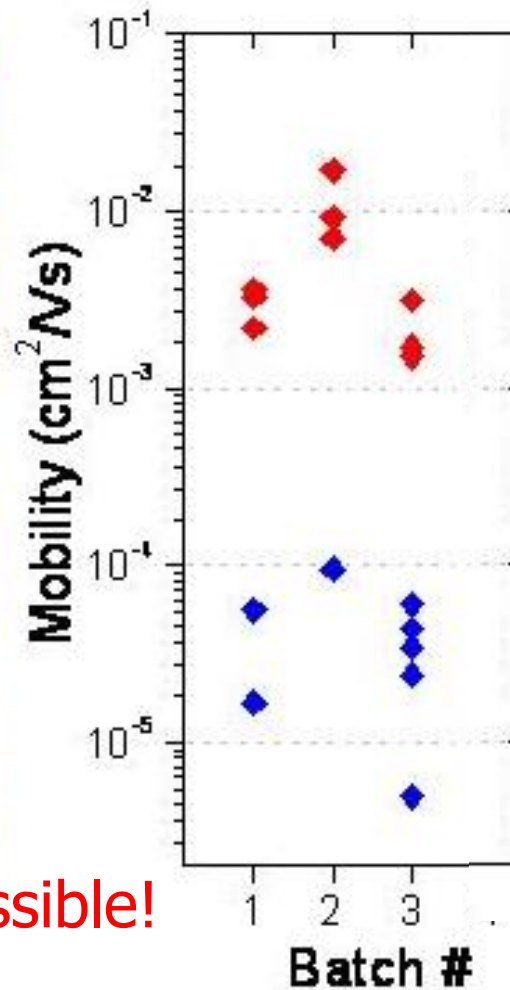
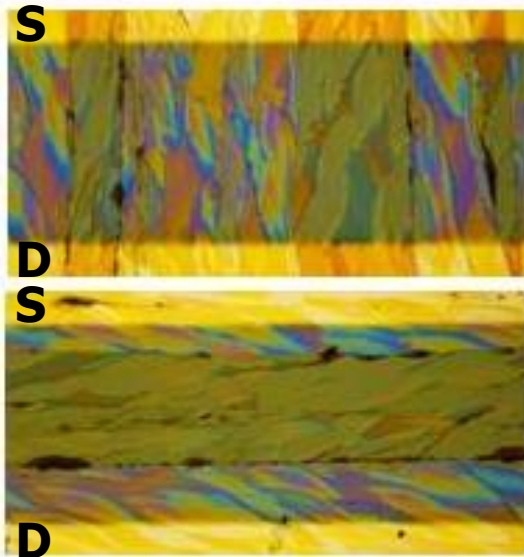
2. Applied Physics: Understand Charge Transport Anisotropy



TFTs with Aligned PDI8-CN2 Films



Charge Transport



High Performance

Low Performance

|| vs. $\perp$ much more efficient

Mobility increase by 3-8x is possible!

2. Applied Physics: Understand Performance Limits

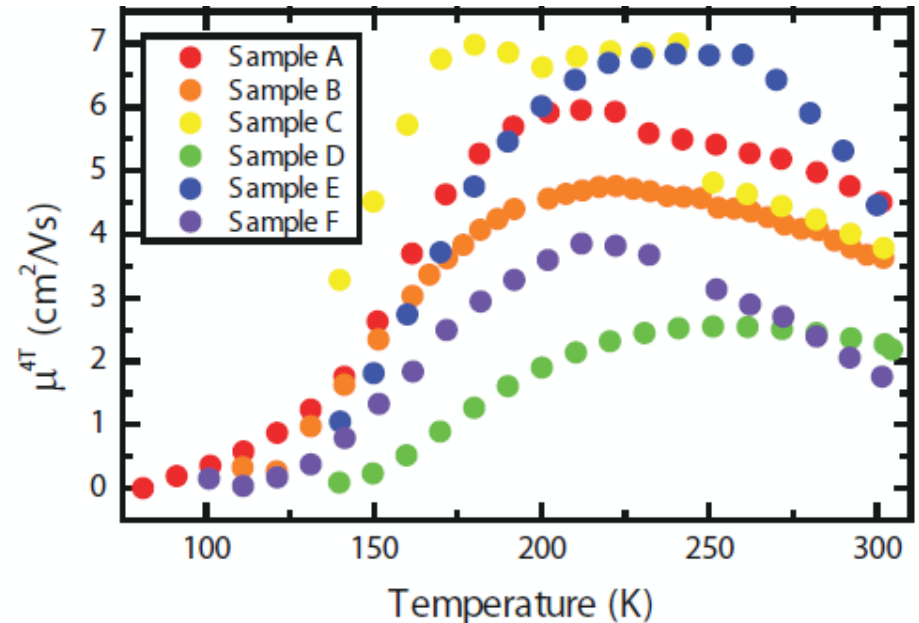
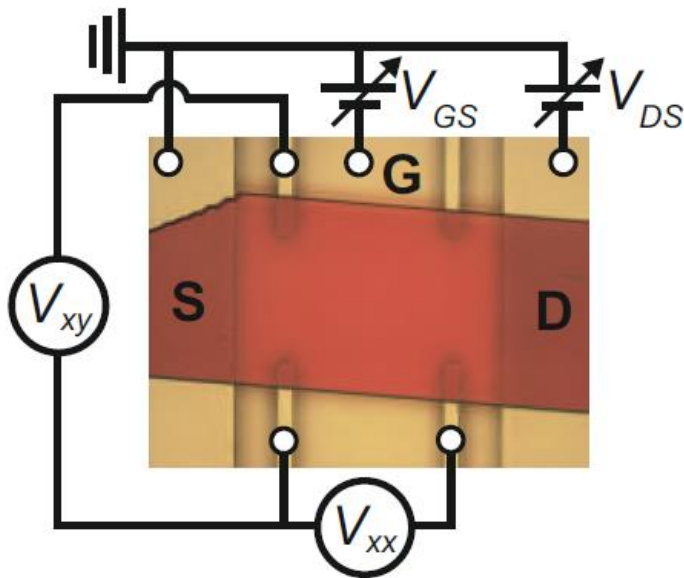
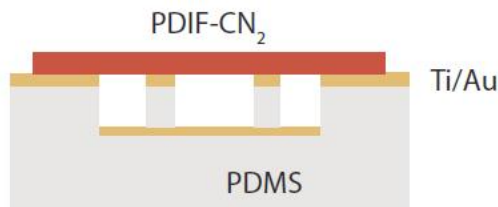
PDIF-CN₂ Single Crystal FETs

- Photolithographically structured neg. resist (SU-8/25)

- Filled with Polydimethylsiloxane (PDMS) elastomer

- 3 nm Ti, 20 nm Au evaporated on PDMS

- Single crystal laminated manually to substrate



> **Band-like transport**
> **Mobility ~ 7 cm²/Vs possible**

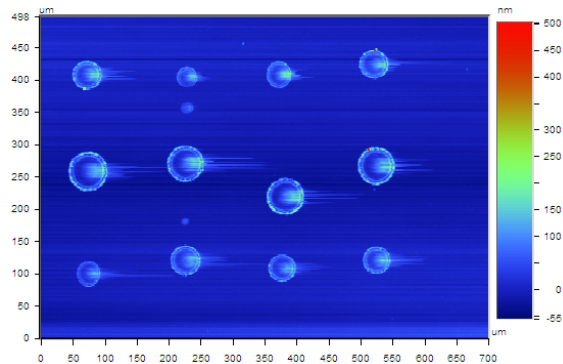
Facchetti, Morpurgo et.al. *Adv. Mater.* **2012**

Takeya, Facchetti *Adv. Mater.* **2011**, 23(32), 3681

Facchetti, Morpurgo et.al. *JACS* **2009**, 131, 2462

3. Process Eng.: Ink-jet Printing Molecular Semiconductors

- **Formulation**
- **Viscosity**
- **Surface Tension**
- **Surface Energy**
- **Printing Speed**
- **Droplet Size**
- **Temperature**

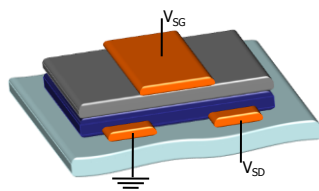
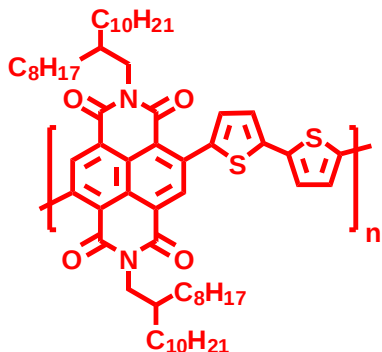


Target OSF morphology

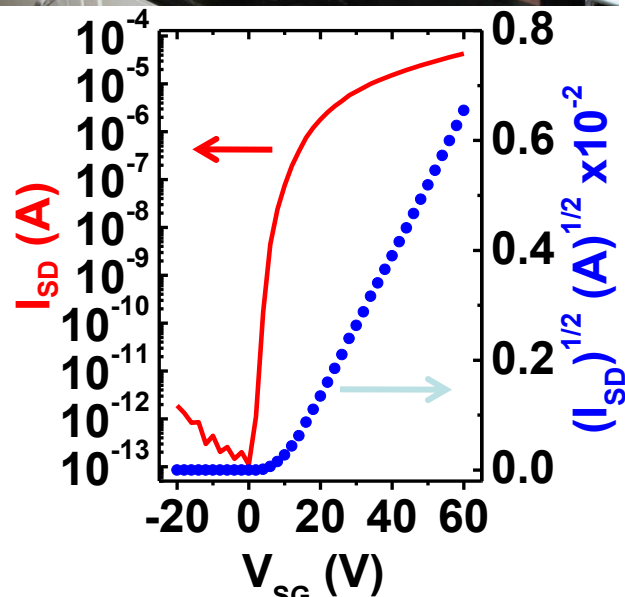
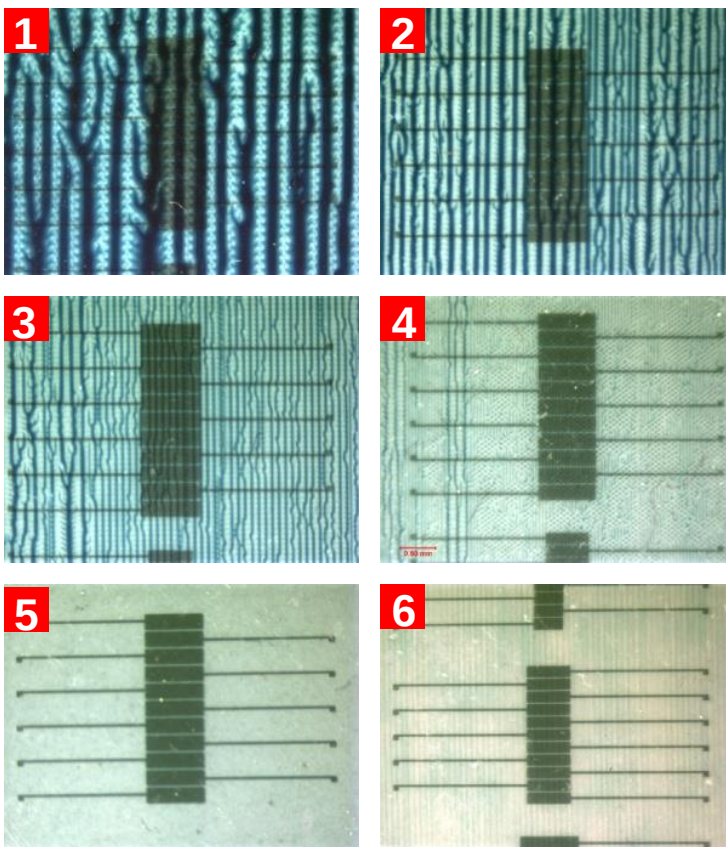
Target OSF morphology



3. Process Eng.: Gravure Printing Polymeric Semiconductors



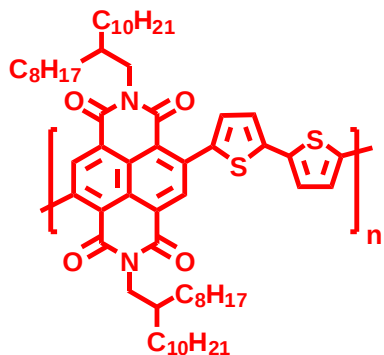
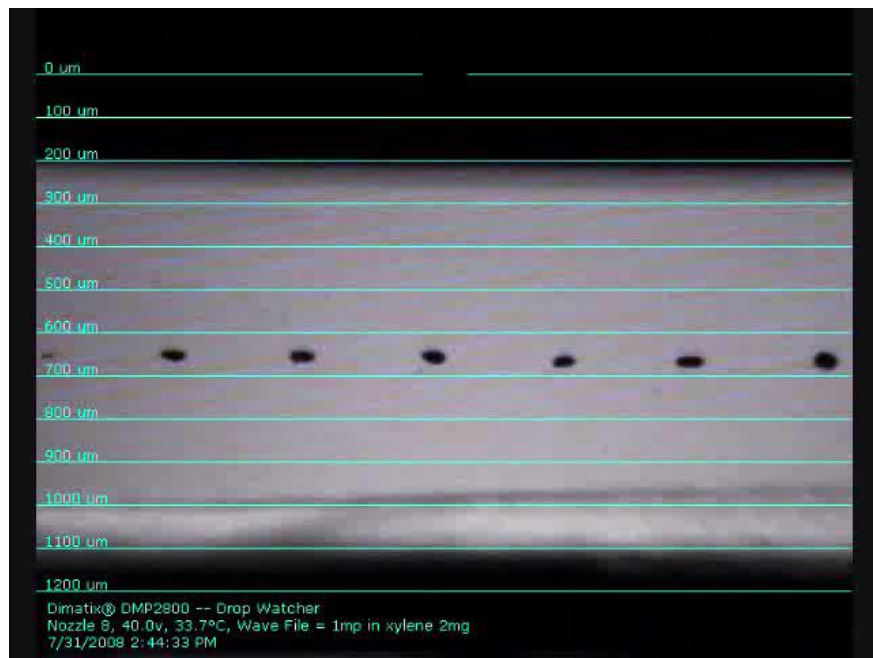
Optimizing semiconductor formulations



$$\mu = 0.2-0.85 \text{ cm}^2/\text{Vs}$$

3. Process Eng.: Printing Polymers vs. Small Molecules

Bad formulation



Mw ~ 60K Da

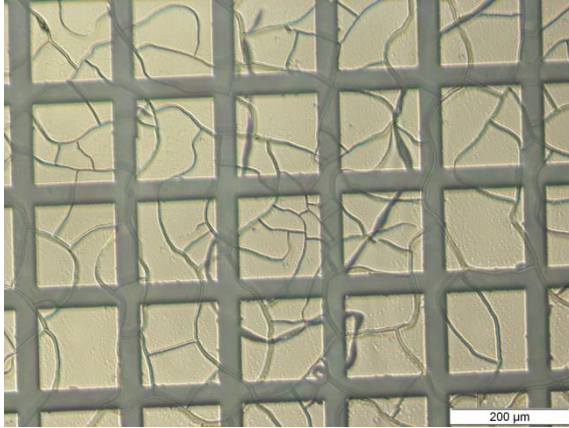
Good formulation



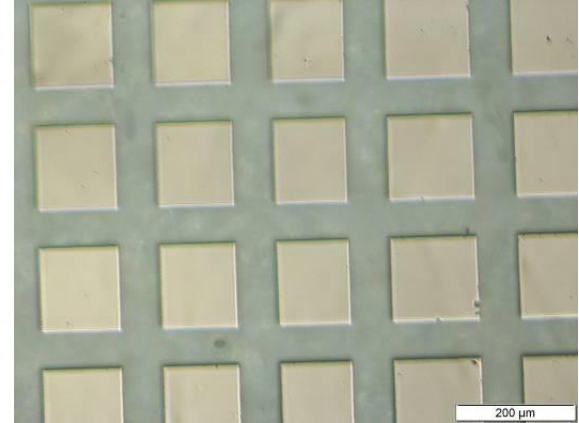
Mw ~ 25K Da

4. Process Eng.: Printing Dielectrics

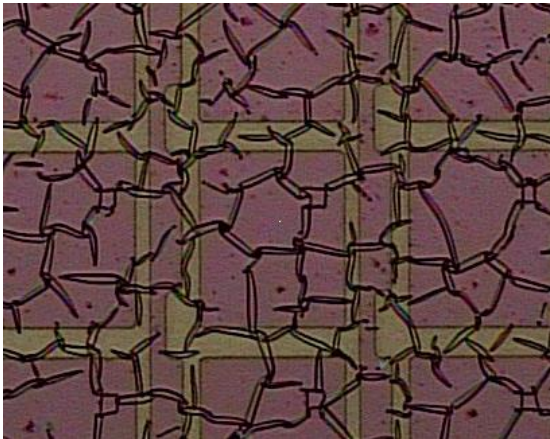
Unoptimized formulation



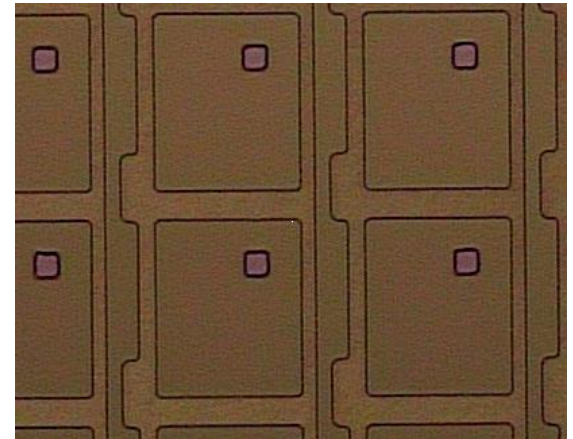
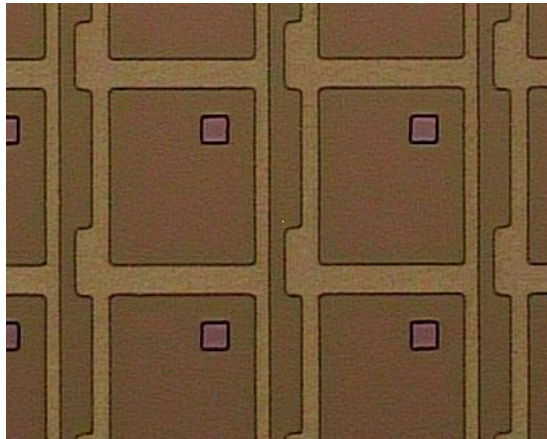
Optimized formulation



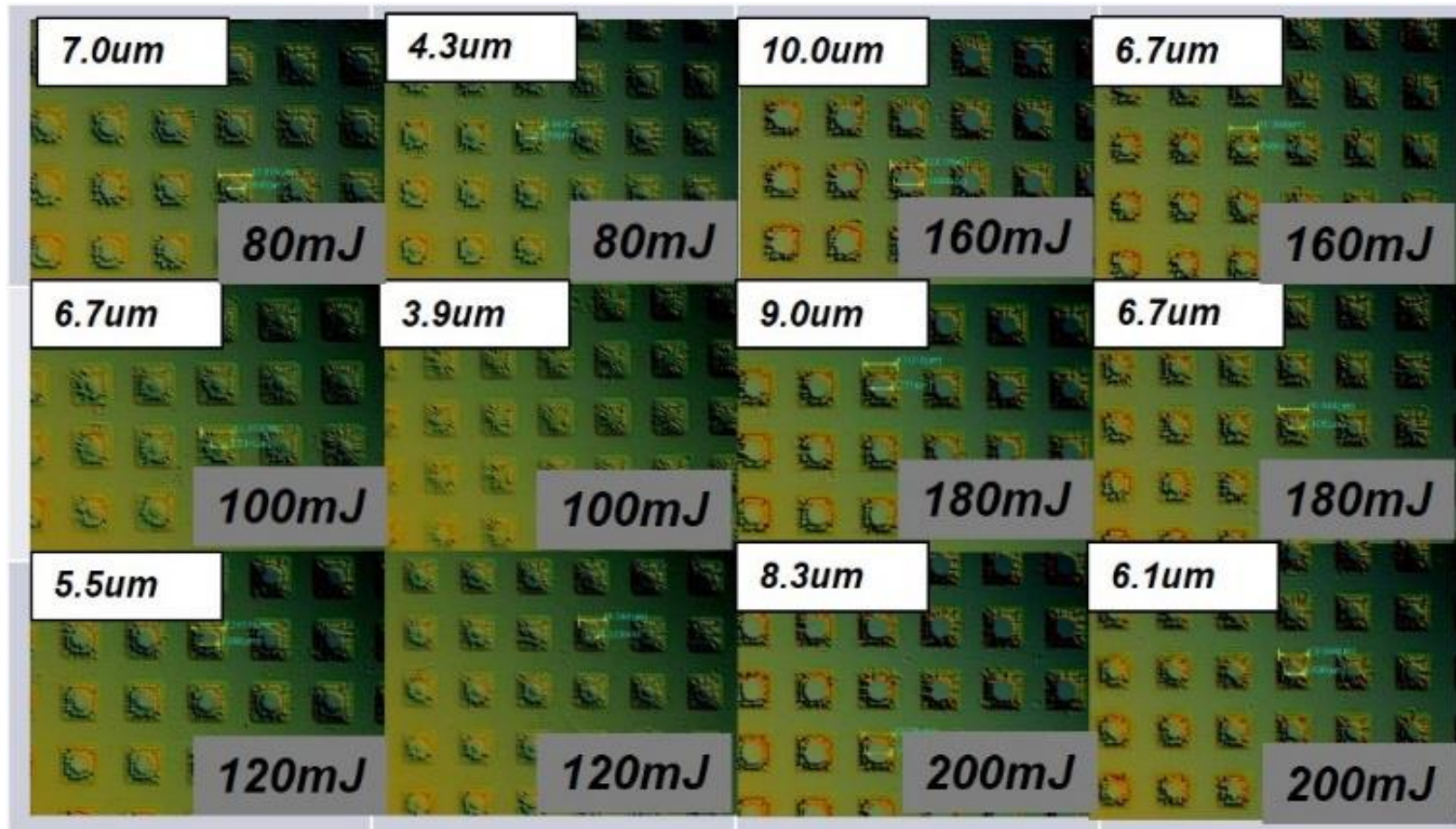
Unoptimized curing



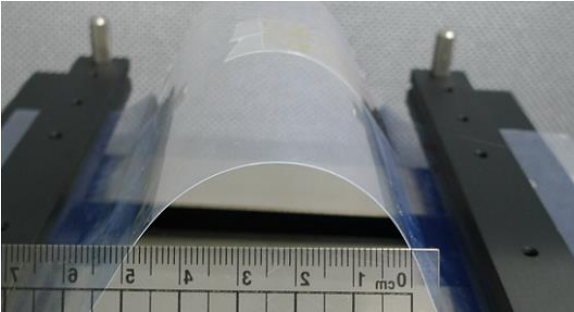
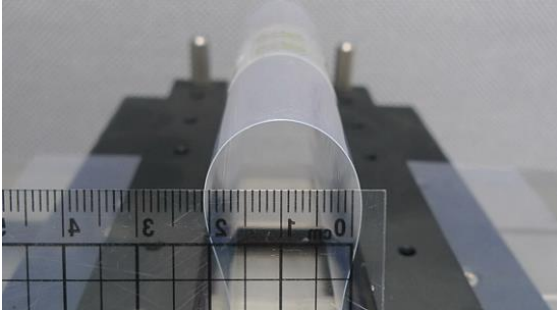
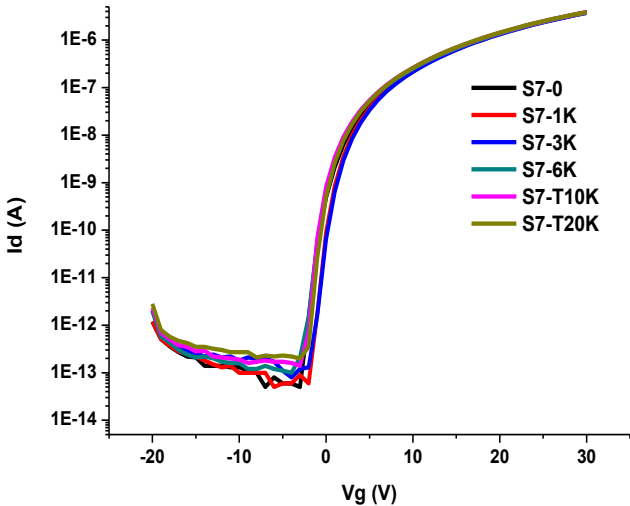
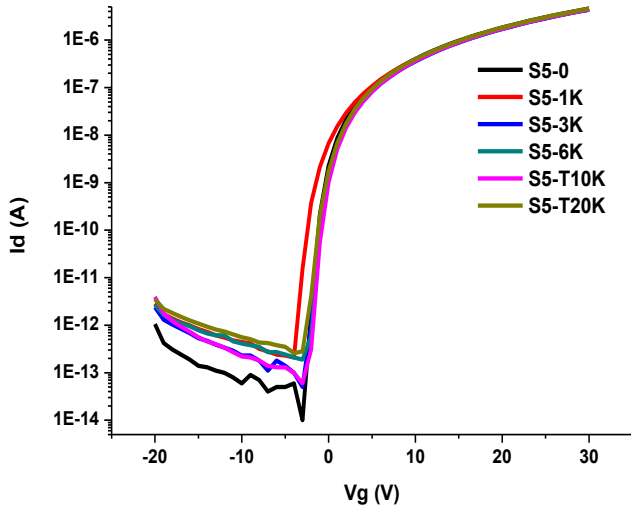
Optimized curing



4. Integration: Multistack deposition, Via Holes



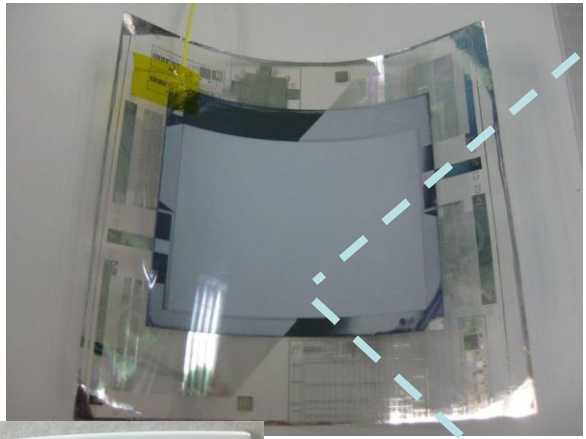
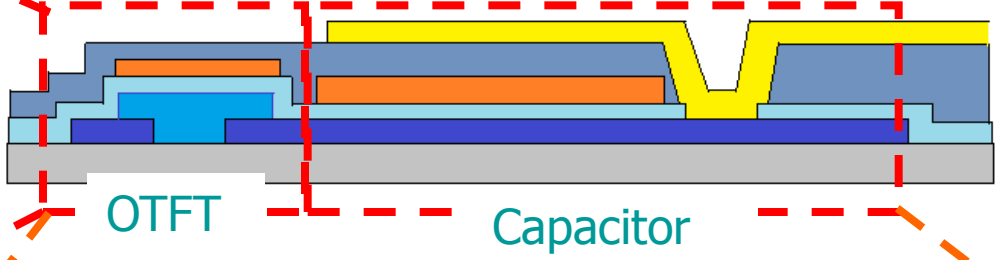
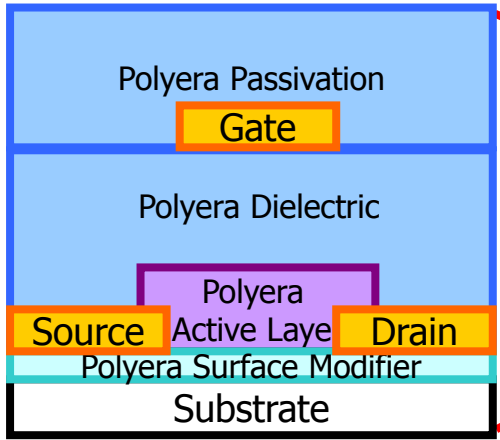
4. Integration: Mechanical stress tests

Bending curve (diameter)	Diameter: 5 cm 	Diameter: 2 cm 
Bending frequency	20 times/min	20 times/mins
Times	Initial→20,000 times	Initial→20,000 times
IV result		

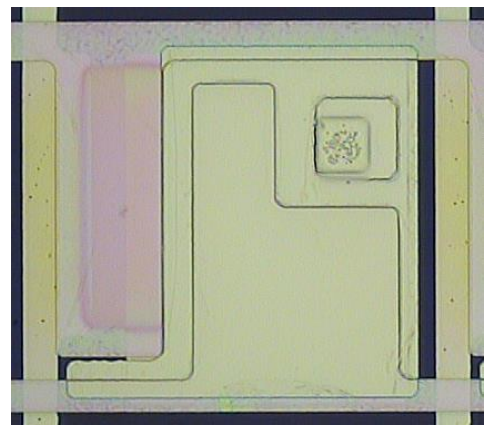
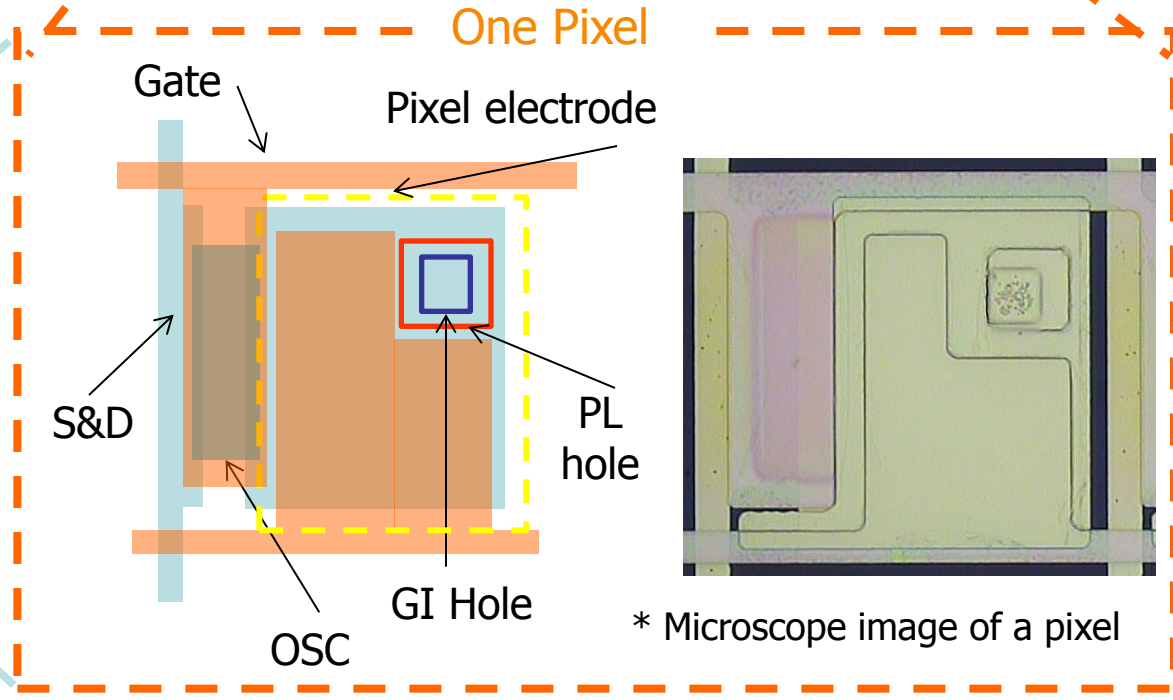
Testing 5 mm at customer sites

4. Prototyping: Flexible Displays

500.000 OTFTs
T < 120 °C



- Polyera 1st gen. backplane for 6" EPD
- (800x600 pixels)



* Microscope image of a pixel

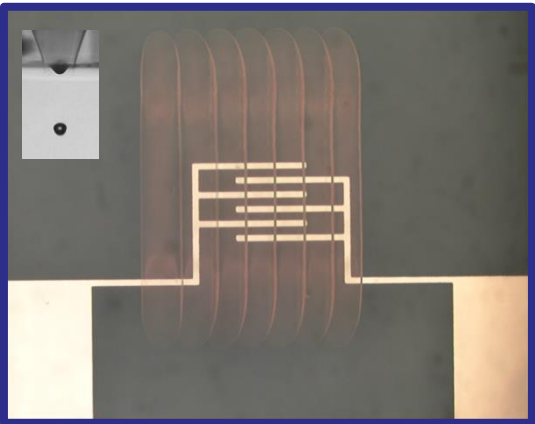


IMG_0965 - Copy (1).mp4

4. Prototyping: Printed Circuits for Sensors

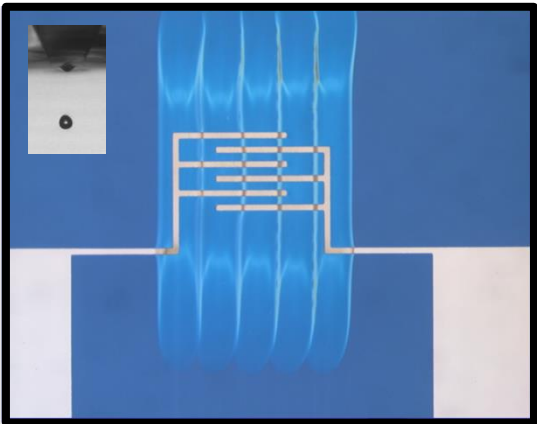
Need p- and n-type semiconductors with comparable performance in printed TFTs

P-channel

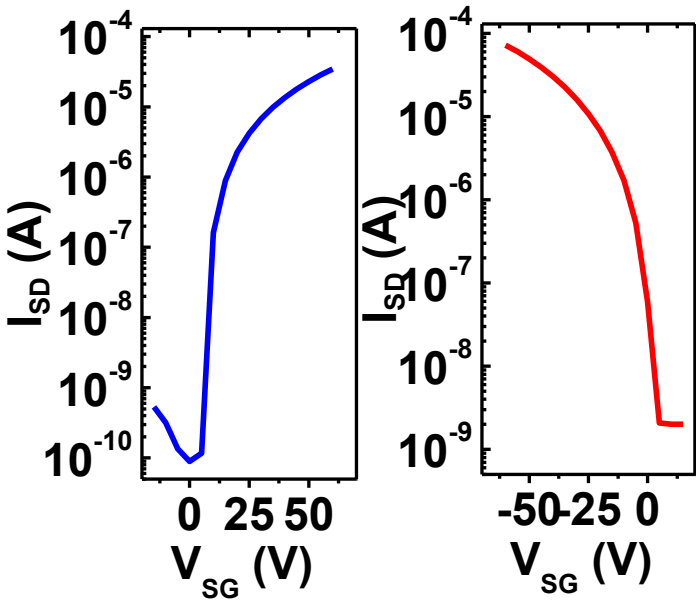


0.75 cm²/Vs

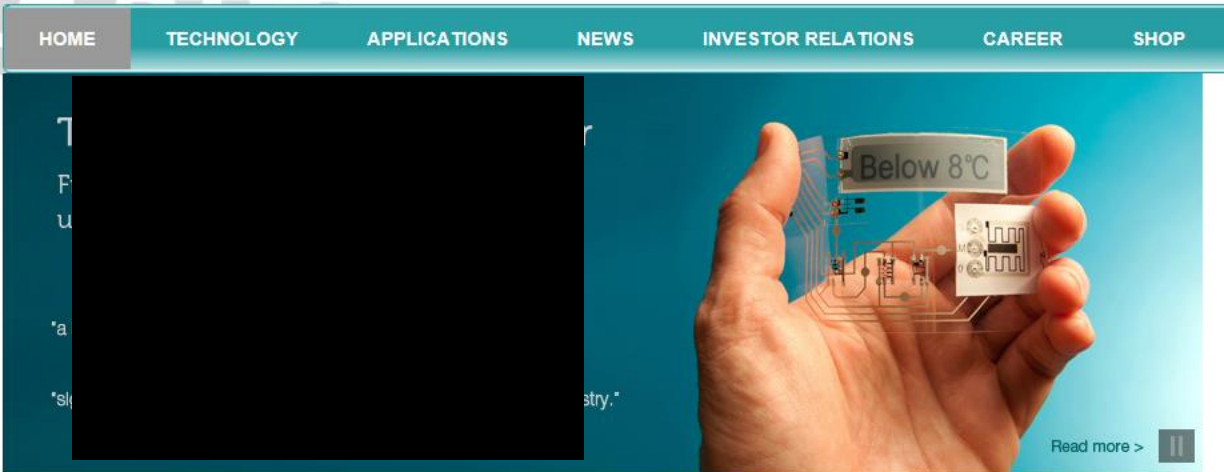
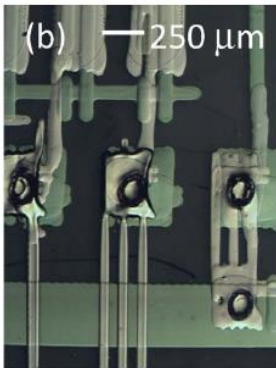
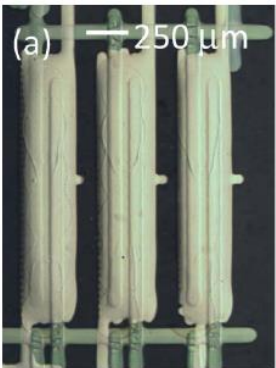
N-channel



0.85 cm²/Vs



Search:

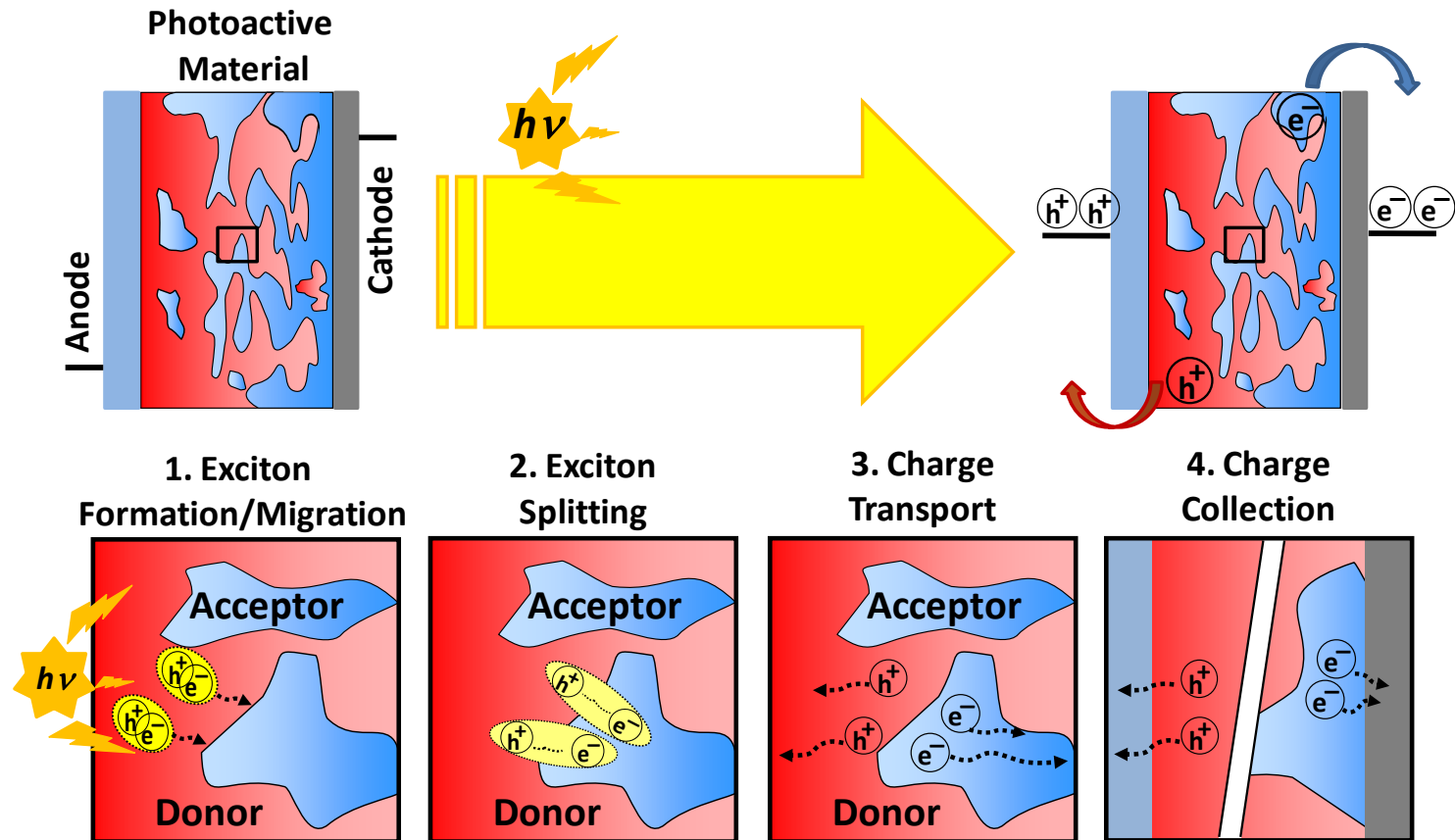


Part 3.

Organic Solar Cells

Organic Photovoltaic Cells

Solar energy into electrical energy (photons to charges)



$$\text{power conversion efficiency } \eta = \frac{\text{electrical power generated}}{\text{incident optical power}}$$

$$= \frac{V_{oc} I_{sc}}{P_{in}} ff$$

Opportunities for Printed Solar Cells



Low power applications
like watches, calculators, etc.

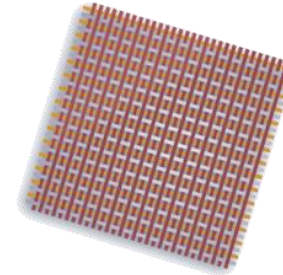
<http://www.citizenwatch.com>

<http://zzd99.en.alibaba.com>

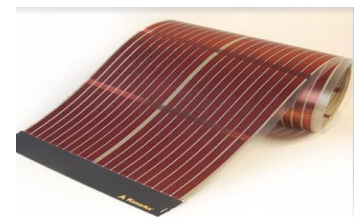


Charge iPods and other portable
devices anywhere, day or night

<http://www.solio.com>



Flexible OPV woven
into a fabric



Flexible solar cells on a military tent

<http://www.afrlhorizons.com/Briefs/Jun04/ML0319.html>



Building integration

PCEs ~ 5 % is sufficient!

Organic Photovoltaic Cells

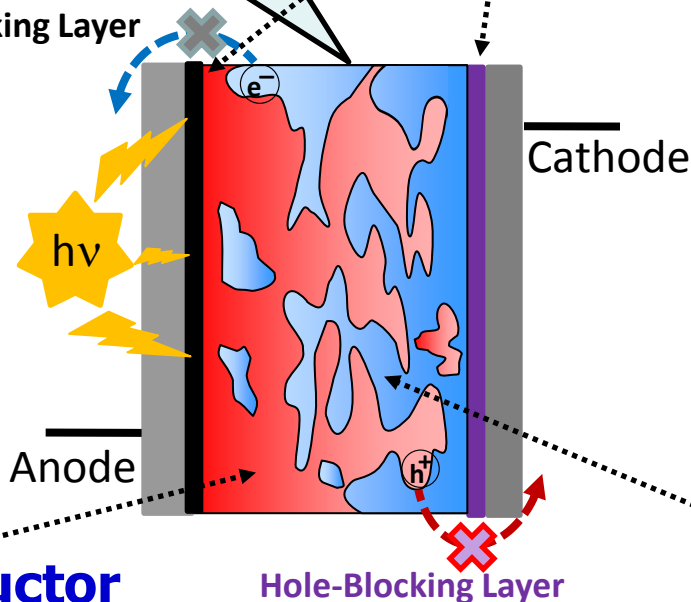


Photoactive Layer
Donor, Acceptors

Interface

van der Boom, Facchetti, *J. Am. Chem. Soc.* **2010**, *132*, 8533
Facchetti, Marks *Nano Letters* **2012**, *12*, 6315

Electron-Blocking Layer



Anode

Cathode

Hole-Blocking Layer

Donor Semiconductor

Facchetti, Marks, Pagani *J. Am. Chem. Soc.*, **2010**, *132*, 4074
Facchetti, Marks, Marrocchi *Adv. Mater* **2011**, *23*, 3827
Facchetti, Marks, Stupp *J. Am. Chem. Soc.*, **2011**, *133*, 8142
Facchetti, Beverina *J. Org. Chem.* **2011**, *28*, 5555
Facchetti, Marks *Chem. Commun.* **2012**, 48(68), 8511
Facchetti, Chen, Marks *Adv. Mater.* **2012**, *24*(17), 2362
Pierre, Facchetti, Arias *J. Appl. Phys.* **2013**, *113*, 154506
Facchetti, Beverina *J. Mater. Chem. A* **2013**, *1*, 2631
Lu, Facchetti *Macromolecules* **2013**, *46*, 3895
Seri, Muccini, Facchetti *Macromolecules* **2013**, *in press*

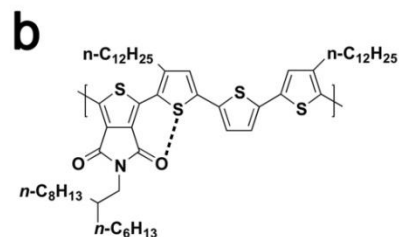
Acceptor Semiconductor / Process

Facchetti, Loi *J. Mater. Chem.* **2010**, *20*, 1317
Loo, Facchetti *Chem. Mater.* **2010**, *22*, 4931
Facchetti, Loi *J. Mater. Chem.* **2011**, *21*, 5891
Shubert, Facchetti, Neher *Adv. En. Mater.* **2012**, *2*, 369
Facchetti, Vaccaro, Marrocchi *En. Envir. Sci.* **2012**, *5*, 8457
Facchetti *Angew. Chem. Inter. Ed.* **2012**, *51*, 3520
Facchetti, Neher *J. Am. Chem. Soc.* **2012**, *134*, 18303
Facchetti *Mater Today* **2013**, *16*, 123

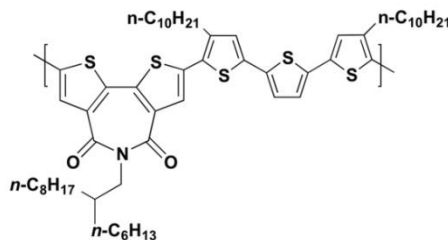
Donor-Acceptor Semiconductor Design

DONOR
(hole semiconductor)

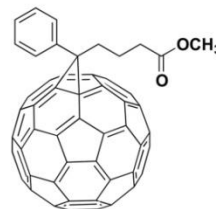
ACCEPTOR
(electron semiconductor)



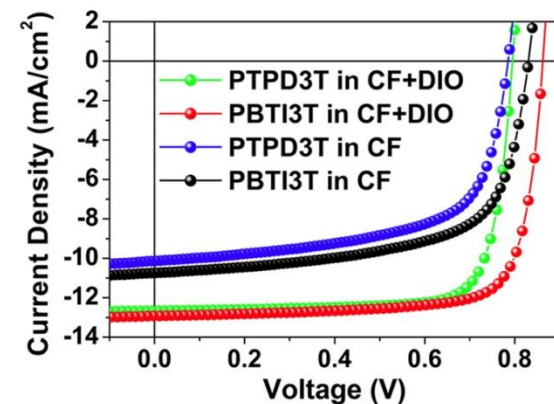
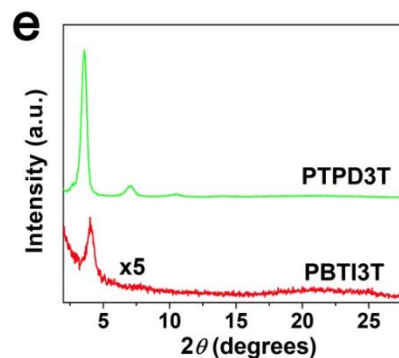
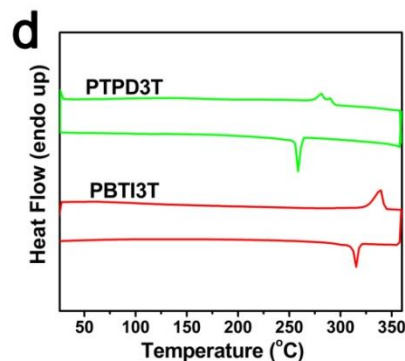
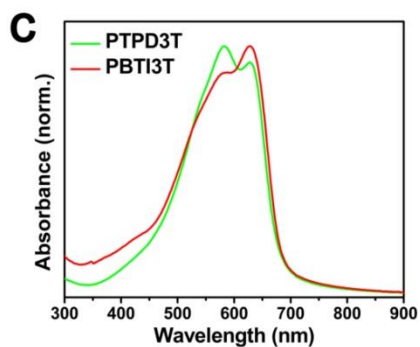
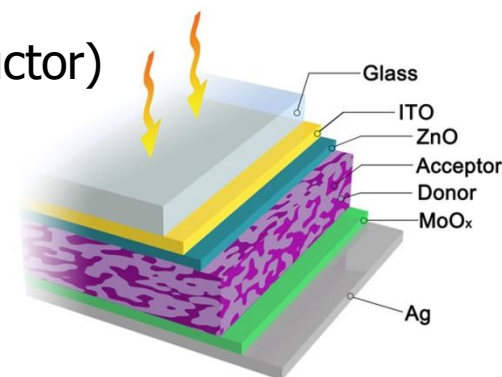
PTPD3T



PBTi3T

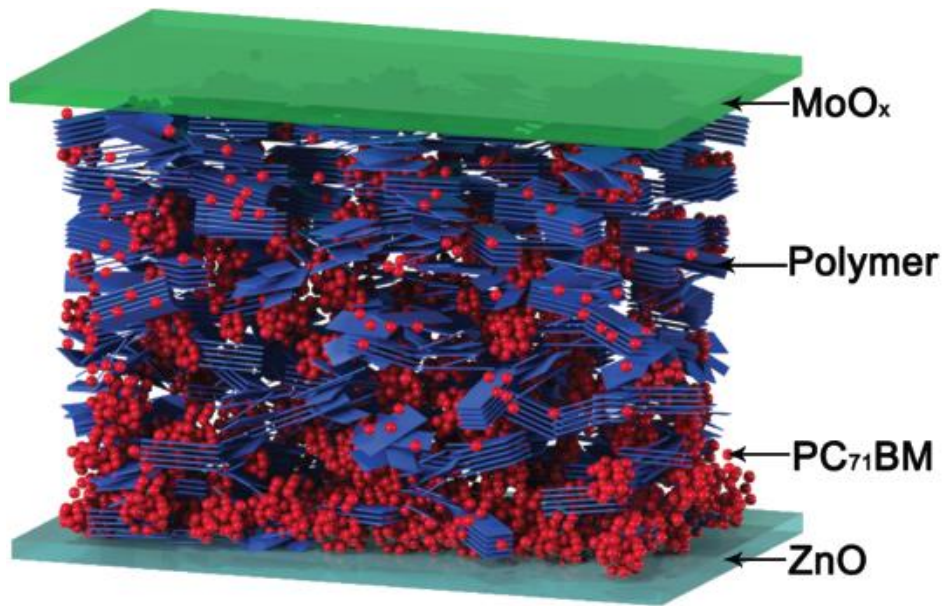


PC₇₁BM



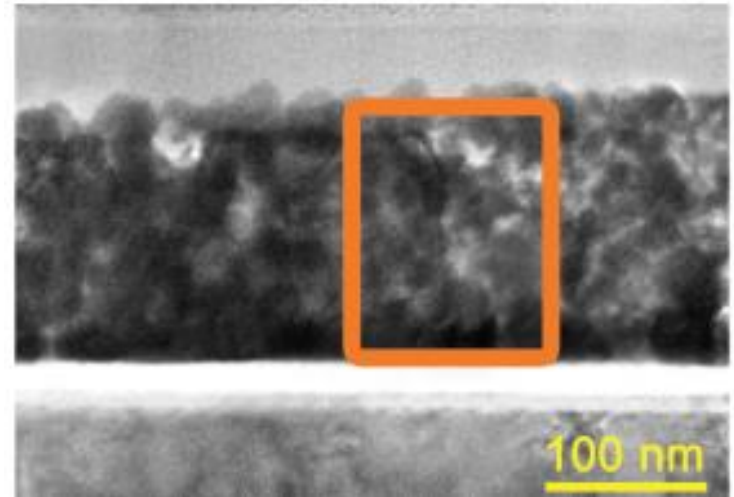
Polymer	μ_h (TFT) (cm ² /Vs)	μ_h (SCLC) (cm ² /Vs)	V_{oc} (V)	J_{cs} (mA/cm ²)	FF (%)	PCE (%)*
PTPD3T	5.87×10^{-2}	1.2×10^{-3}	0.795	12.5	79.6	7.90
PBTi3T	2.74×10^{-3}	1.5×10^{-3}	0.859	12.9	77.8	8.66

Understand/Control Protoactive Blend Microstructure



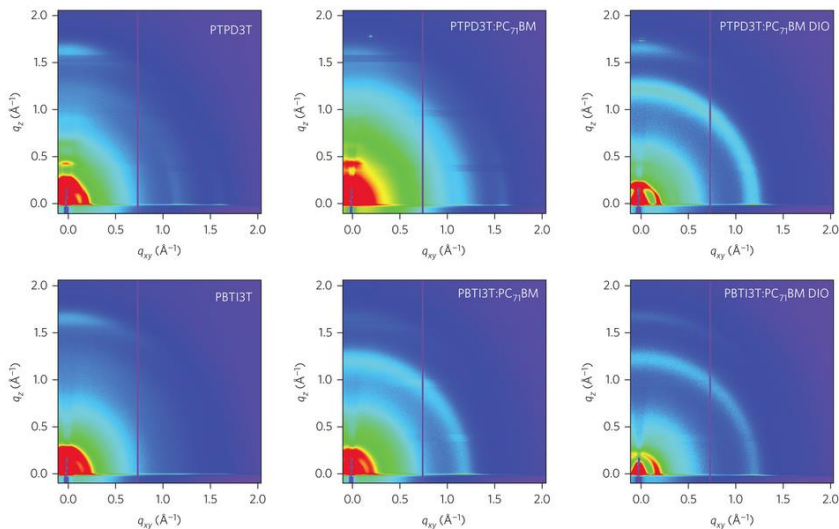
Cross-sectional TEM specimen (FIB) prepared:

- Darker contrast may indicate PC₇₁BM
- Preferred aggregation at bottom (ZnO) interface



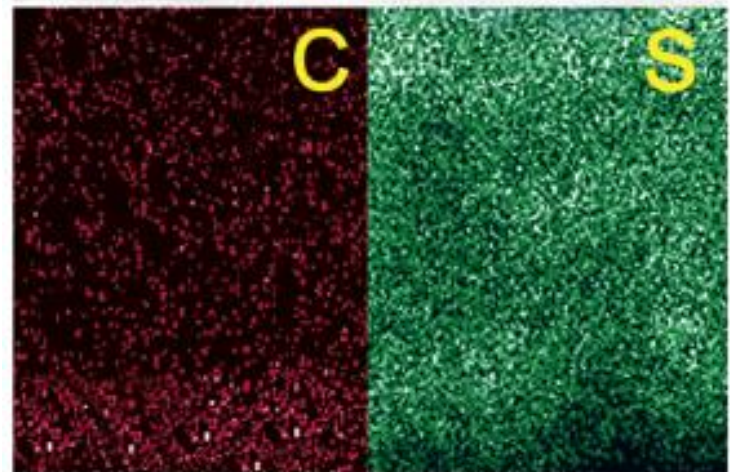
WAXRD

- Crystalline, face-on oriented



EDS mapping in active layer

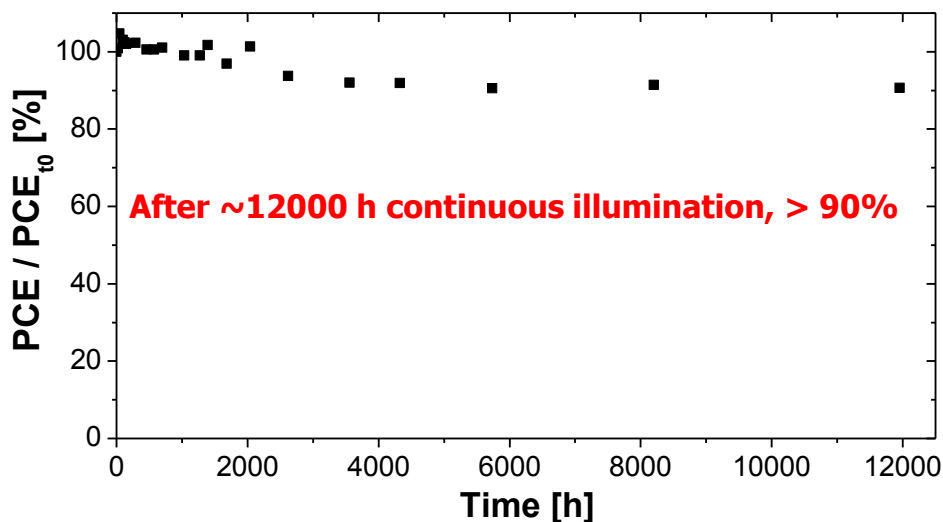
- More C and less S content near ZnO interface



Understand/Control Processing, Monitor Stability

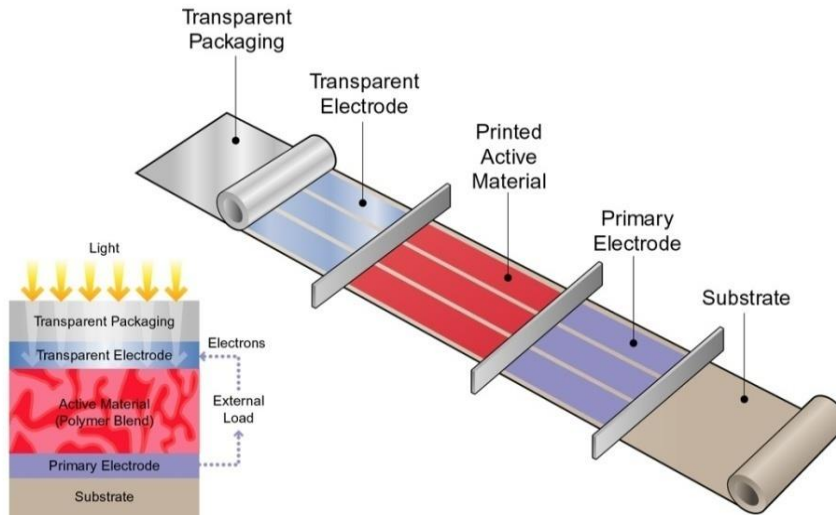
- Active layer coated under N_2 or air
- Spin casting and doctor blading
- Same performance in air and N_2

PCE $\sim$ 8%



Printing OPV Modules

- Technology Overview



- Patented roll-to-roll process:
 - Continuous printing/coating
 - Flexible substrates
 - Lower capital & labor costs
 - Low-temp/low-energy/low carbon manufacturing
 - Uses existing coating & printing equipment



Conclusions

Challenges

Printed TFTs, Circuits

- Scale-up current generation of materials
- Engineering the process in a FAB line
- Develop second-generation material set

Organic Solar Cells

- Develop suitable donor-acceptor semiconductors
- Long-term stability
- Cost-effective encapsulation

Opportunities

- Understand/control light/transport phenomena in soft matter
- Create a new industry

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